

# Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

# **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

# Programmable Precision References

The TL431, A, B integrated circuits are three–terminal programmable shunt regulator diodes. These monolithic IC voltage references operate as a low temperature coefficient zener which is programmable from  $V_{ref}$  to 36 V with two external resistors. These devices exhibit a wide operating current range of 1.0 mA to 100 mA with a typical dynamic impedance of 0.22  $\Omega$ . The characteristics of these references make them excellent replacements for zener diodes in many applications such as digital voltmeters, power supplies, and op amp circuitry. The 2.5 V reference makes it convenient to obtain a stable reference from 5.0 V logic supplies, and since the TL431, A, B operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

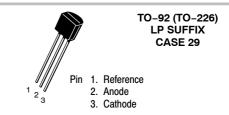
#### **Features**

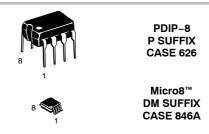
- Programmable Output Voltage to 36 V
- Voltage Reference Tolerance: ±0.4%, Typ @ 25°C (TL431B)
- Low Dynamic Output Impedance, 0.22 Ω Typical
- Sink Current Capability of 1.0 mA to 100 mA
- Equivalent Full-Range Temperature Coefficient of 50 ppm/°C Typical
- Temperature Compensated for Operation over Full Rated Operating Temperature Range
- Low Output Noise Voltage
- Pb-Free Packages are Available

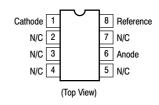


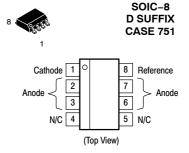
#### ON Semiconductor®

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This is an internally modified SOIC–8 package. Pins 2, 3, 6 and 7 are electrically common to the die attach flag. This internal lead frame modification increases power dissipation capability when appropriately mounted on a printed circuit board. This modified package conforms to all external dimensions of the standard SOIC–8 package.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

#### **DEVICE MARKING INFORMATION**

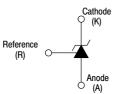
See general marking information in the device marking section on page 15 of this data sheet.

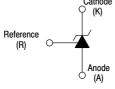
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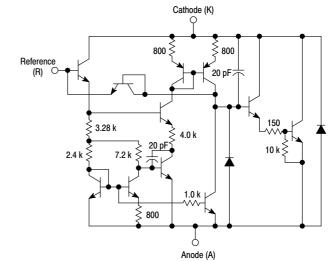
#### **Symbol**

### Representative Schematic Diagram

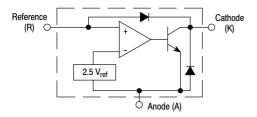
Component values are nominal







#### **Representative Block Diagram**



This device contains 12 active transistors.

#### MAXIMUM RATINGS (Full operating ambient temperature range applies, unless otherwise noted.)

Rating	Symbol	Value	Unit
Cathode to Anode Voltage	V <sub>KA</sub>	37	V
Cathode Current Range, Continuous	I <sub>K</sub>	-100 to +150	mA
Reference Input Current Range, Continuous	I <sub>ref</sub>	-0.05 to +10	mA
Operating Junction Temperature	TJ	150	°C
Operating Ambient Temperature Range TL431I, TL431AI, TL431BI TL431C, TL431AC, TL431BC NCV431AI, NCV431B, TL431BV	T <sub>A</sub>	-40 to +85 0 to +70 -40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Total Power Dissipation @ T <sub>A</sub> = 25°C  Derate above 25°C Ambient Temperature  D, LP Suffix Plastic Package  P Suffix Plastic Package  DM Suffix Plastic Package	P <sub>D</sub>	0.70 1.10 0.52	W
Total Power Dissipation @ T <sub>C</sub> = 25°C  Derate above 25°C Case Temperature  D, LP Suffix Plastic Package  P Suffix Plastic Package	P <sub>D</sub>	1.5 3.0	W
ESD Rating	HBM MM	>2000 >200	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **RECOMMENDED OPERATING CONDITIONS**

Condition		Min	Max	Unit
Cathode to Anode Voltage	$V_{KA}$	$V_{ref}$	36	V
Cathode Current	Ι <sub>Κ</sub>	1.0	100	mA

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	D, LP Suffix Package	P Suffix Package	DM Suffix Package	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	178	114	240	°C/W
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	83	41	-	°C/W

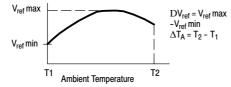
#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted.)

			TL431I			TL431C		
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Reference Input Voltage (Figure 1) $V_{KA} = V_{ref}, I_K = 10 \text{ mA}$ $T_A = 25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high} \text{ (Note 1)}$	V <sub>ref</sub>	2.44 2.41	2.495 -	2.55 2.58	2.44 2.423	2.495 -	2.55 2.567	V
Reference Input Voltage Deviation Over Temperature Range (Figure 1, Notes 1, 2) V <sub>KA</sub> = V <sub>ref</sub> , I <sub>K</sub> = 10 mA	$\Delta V_{ m ref}$	-	7.0	30	-	3.0	17	mV
Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 10$ mA (Figure 2), $\Delta V_{KA} = 10$ V to $V_{ref}$ $\Delta V_{KA} = 36$ V to 10 V	$rac{\Delta V_{ m ref}}{\Delta V_{ m KA}}$	- -	-1.4 -1.0	-2.7 -2.0	- -	-1.4 -1.0	-2.7 -2.0	mV/V
Reference Input Current (Figure 2) $I_K = 10 \text{ mA, R1} = 10 \text{ k, R2} = \infty$ $T_A = 25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high} \text{ (Note 1)}$	I <sub>ref</sub>	- -	1.8 -	4.0 6.5	- -	1.8 -	4.0 5.2	μΑ
Reference Input Current Deviation Over Temperature Range (Figure 2, Note 1, 4) I <sub>K</sub> = 10 mA, R1 = 10 k, R2 = ∞	$\Delta I_{ref}$	_	0.8	2.5	_	0.4	1.2	μΑ
Minimum Cathode Current For Regulation V <sub>KA</sub> = V <sub>ref</sub> (Figure 1)	I <sub>min</sub>	-	0.5	1.0	-	0.5	1.0	mA
Off–State Cathode Current (Figure 3) V <sub>KA</sub> = 36 V, V <sub>ref</sub> = 0 V	I <sub>off</sub>	-	20	1000	_	20	1000	nA
Dynamic Impedance (Figure 1, Note 3) $V_{KA} = V_{ref}, \Delta I_K = 1.0 \text{ mA to } 100 \text{ mA}$ $f \leq 1.0 \text{ kHz}$	Z <sub>KA</sub>	_	0.22	0.5	_	0.22	0.5	Ω

1.  $T_{low}$  = -40°C for TL431AIP TL431AILP, TL431IP, TL431BID, TL431BID, TL431BID, TL431BIDM, TL431AIDM, TL431BIDM, TL431ACDM, TL431ACDM, TL431ACDM, TL431BCDM, TL431BCDM

Thigh = +85°C for TL431AIP, TL431AILP, TL431IP, TL431IBID, TL431BID, TL431BILP, TL431BIDM, TL431AIDM, TL431AIDM, TL431BIDM = +70°C for TL431ACP, TL431ACLP, TL431CP, TL431ACD, TL431BCD, TL431BCP, TL431BCDM, TL431BCDM

2. The deviation parameter ΔV<sub>ref</sub> is defined as the difference between the maximum and minimum values obtained over the full operating ambient temperature range that applies.



The average temperature coefficient of the reference input voltage,  $\alpha \text{V}_{\text{ref}}$  is defined as:

$$V_{ref} \frac{ppm}{^{\circ}C} = \frac{\left(\frac{\Delta V_{ref}}{V_{ref} @ 25^{\circ}C}\right) \times 10^{6}}{\Delta T_{A}} = \frac{\Delta V_{ref} \times 10^{6}}{\Delta T_{A} (V_{ref} @ 25^{\circ}C)}$$

 $\alpha V_{ref}$  can be positive or negative depending on whether  $V_{ref}$  Min or  $V_{ref}$  Max occurs at the lower ambient temperature. (Refer to Figure 6.)

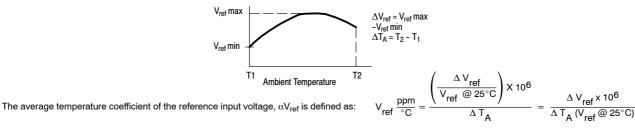
Example : 
$$\Delta V_{ref} = 8.0 \text{ mV}$$
 and slope is positive, 
$$V_{ref} @ 25^{\circ}C = 2.495 \text{ V}, \Delta T_{A} = 70^{\circ}C$$
  $\alpha V_{ref} = \frac{0.008 \times 10^{6}}{70 \ (2.495)} = 45.8 \text{ ppm/}^{\circ}C$ 

3. The dynamic impedance  $Z_{KA}$  is defined as:  $|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$ . When the device is programmed with two external resistors, R1 and R2, (refer to Figure 2) the total dynamic impedance of the circuit is defined as:  $|Z_{KA}'| \approx |Z_{KA}| \left(1 + \frac{R1}{R2}\right)$ 

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted.)

		TL431	AI / NC\	/431AI	7	L431A0	<b>.</b>	TI	3C / TL4 L431BV CV431B	1	
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Reference Input Voltage (Figure 1) $V_{KA} = V_{ref}, I_K = 10 \text{ mA}$ $T_A = 25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high}$	V <sub>ref</sub>	2.47 2.44	2.495 –	2.52 2.55	2.47 2.453	2.495 -	2.52 2.537	2.485 2.475	2.495 2.495	2.505 2.515	V
Reference Input Voltage Deviation Over Temperature Range (Figure 1, Notes 4, 5) V <sub>KA</sub> = V <sub>ref</sub> , I <sub>K</sub> = 10 mA	$\Delta V_{ref}$	_	7.0	30	_	3.0	17	-	3.0	17	mV
Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 10$ mA (Figure 2), $\Delta V_{KA} = 10$ V to $V_{ref}$ $\Delta V_{KA} = 36$ V to 10 V	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$		-1.4 -1.0	-2.7 -2.0	-	-1.4 -1.0	-2.7 -2.0		-1.4 -1.0	-2.7 -2.0	mV/V
Reference Input Current (Figure 2) $I_K = 10$ mA, R1 = 10 k, R2 = $\infty$ $T_A = 25^{\circ}C$ $T_A = T_{low}$ to $T_{high}$ (Note 4)	I <sub>ref</sub>	_ _	1.8 -	4.0 6.5	- -	1.8	4.0 5.2	_ _	1.1	2.0 4.0	μΑ
Reference Input Current Deviation Over Temperature Range (Figure 2, Note 4) I <sub>K</sub> = 10 mA, R1 = 10 k, R2 = ∞	$\Delta I_{ref}$	_	0.8	2.5	-	0.4	1.2	-	0.8	2.5	μΑ
Minimum Cathode Current For Regulation V <sub>KA</sub> = V <sub>ref</sub> (Figure 1)	I <sub>min</sub>	-	0.5	1.0	_	0.5	1.0	-	0.5	1.0	mA
Off–State Cathode Current (Figure 3) V <sub>KA</sub> = 36 V, V <sub>ref</sub> = 0 V	I <sub>off</sub>	_	20	1000		20	1000		0.23	500	nA
Dynamic Impedance (Figure 1, Note 6) $V_{KA} = V_{ref}$ , $\Delta I_{K} = 1.0$ mA to 100 mA $f \le 1.0$ kHz	Z <sub>KA</sub>	_	0.22	0.5	-	0.22	0.5	-	0.14	0.3	Ω

- 4. T<sub>low</sub> = -40°C for TL431AIP TL431AIP, TL431IP, TL431BID, TL431BIP, TL431BIP, TL431BIP, TL431BIP, TL431BIDM, TL431AIDM, TL431DM, TL431BIDM, NCV431AIDMR2, NCV431AIDR2
  - 0°C for TL431ACP, TL431ACLP, TL431CP, TL431CD, TL431CD, TL431ACD, TL431BCD, TL431BCP, TL431BCLP, TL431CDM, TL431ACDM, TL431BCDM
  - Thigh = +85°C for TL431AIP, TL431IP, TL431IP, TL431BID, TL431BIP, TL431BIP, TL431BIP, TL431BIDM, TL431BIDM, TL431AIDM, TL TL431BCDM
    - = +125°C TL431BV, NCV431AIDMR2, NCV431AIDR2, NCV431BVDMR2G
- 5. The deviation parameter ΔV<sub>ref</sub> is defined as the difference between the maximum and minimum values obtained over the full operating ambient temperature range that applies.

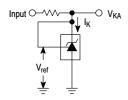


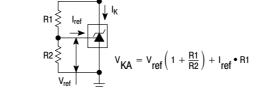
 $\alpha V_{ref}$  can be positive or negative depending on whether  $V_{ref}$  Min or  $V_{ref}$  Max occurs at the lower ambient temperature. (Refer to Figure 6.)

Example : 
$$\Delta V_{ref} = 8.0 \text{ mV}$$
 and slope is positive,  $V_{ref} @ 25^{\circ}C = 2.495 \text{ V}, \Delta T_{A} = 70^{\circ}C$   $\alpha V_{ref} = \frac{0.008 \times 10^{6}}{70 \ (2.495)} = 45.8 \text{ ppm/}^{\circ}C$ 

- 6. The dynamic impedance  $Z_{KA}$  is defined as  $|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$  When the device is programmed with two external resistors, R1 and R2, (refer
- to Figure 2) the total dynamic impedance of the circuit is defined as:  $|Z_{KA}| \approx |Z_{KA}| \left(1 + \frac{R1}{R2}\right)$ 7. NCV431AIDMR2, NCV431BVDMR2G  $T_{low} = -40^{\circ}$ C,  $T_{high} = +125^{\circ}$ C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

Input O





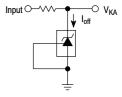


Figure 1. Test Circuit for  $V_{KA} = V_{ref}$ 

Figure 2. Test Circuit for  $V_{KA} > V_{ref}$ 

Figure 3. Test Circuit for Ioff

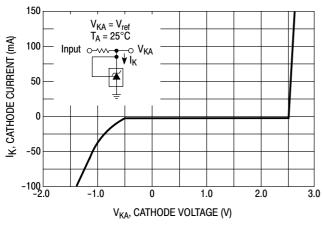


Figure 4. Cathode Current versus Cathode Voltage

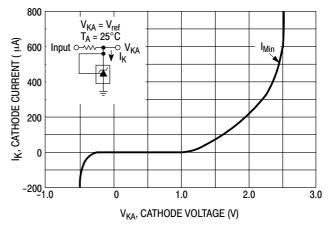


Figure 5. Cathode Current versus Cathode Voltage

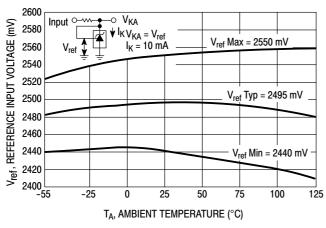


Figure 6. Reference Input Voltage versus Ambient Temperature

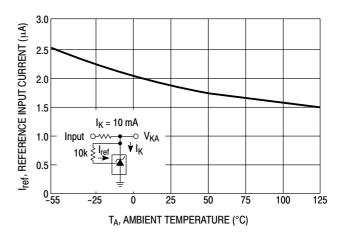


Figure 7. Reference Input Current versus Ambient Temperature

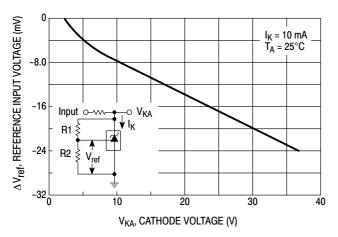


Figure 8. Change in Reference Input Voltage versus Cathode Voltage

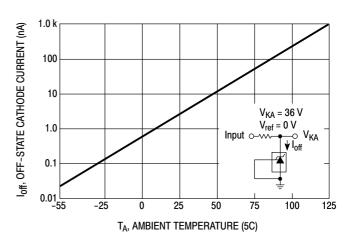


Figure 9. Off-State Cathode Current versus Ambient Temperature

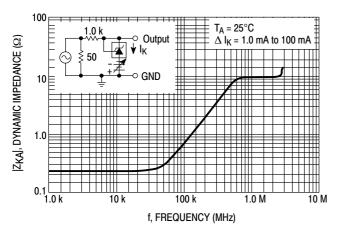


Figure 10. Dynamic Impedance versus Frequency

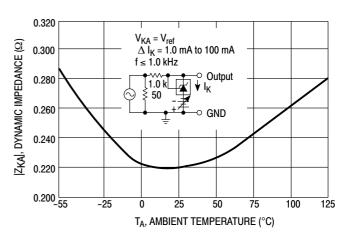


Figure 11. Dynamic Impedance versus Ambient Temperature

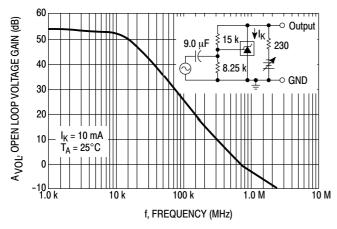


Figure 12. Open-Loop Voltage Gain versus Frequency

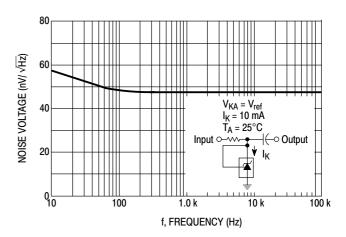


Figure 13. Spectral Noise Density

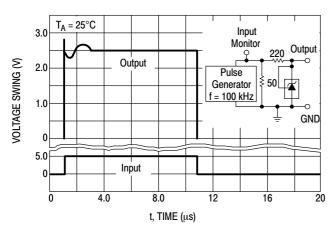


Figure 14. Pulse Response

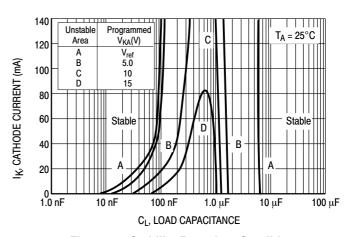


Figure 15. Stability Boundary Conditions

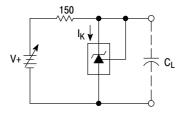


Figure 16. Test Circuit For Curve A of Stability Boundary Conditions

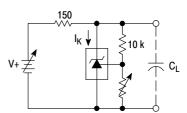


Figure 17. Test Circuit For Curves B, C, And D of Stability Boundary Conditions

#### **TYPICAL APPLICATIONS**

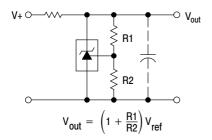


Figure 18. Shunt Regulator

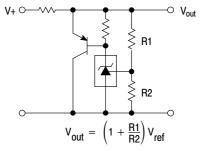


Figure 19. High Current Shunt Regulator

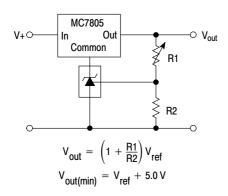


Figure 20. Output Control for a Three–Terminal Fixed Regulator

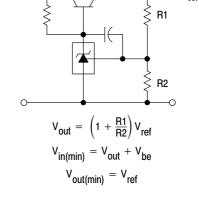


Figure 21. Series Pass Regulator

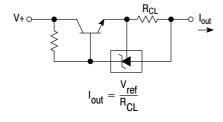


Figure 22. Constant Current Source

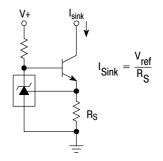


Figure 23. Constant Current Sink

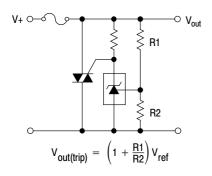


Figure 24. TRIAC Crowbar

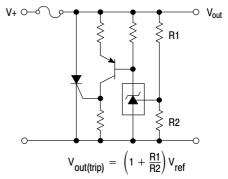
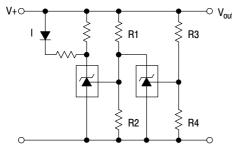


Figure 25. SRC Crowbar



L.E.D. indicator is 'on' when V+ is between the upper and lower limits.

$$\begin{aligned} \text{Lower Limit} &= \left(1 + \frac{R1}{R2}\right) V_{ref} \\ \text{Upper Limit} &= \left(1 + \frac{R3}{R4}\right) V_{ref} \end{aligned}$$

Figure 26. Voltage Monitor

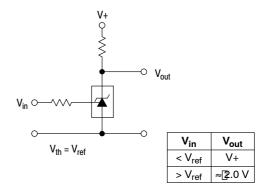


Figure 27. Single–Supply Comparator with Temperature–Compensated Threshold

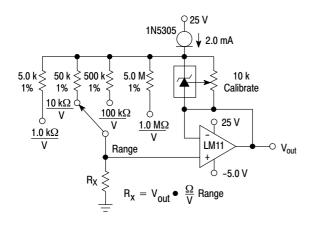


Figure 28. Linear Ohmmeter

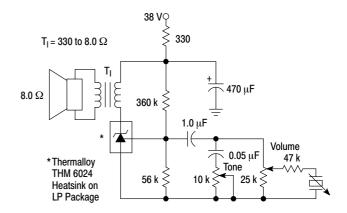


Figure 29. Simple 400 mW Phono Amplifier

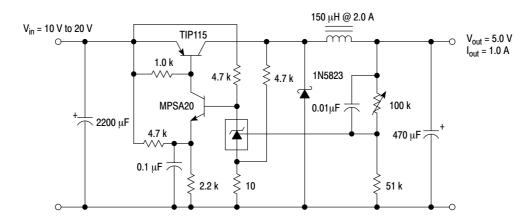


Figure 30. High Efficiency Step-Down Switching Converter

Test	Conditions	Results
Line Regulation	$V_{in} = 10 \text{ V to } 20 \text{ V}, I_0 = 1.0 \text{ A}$	53 mV (1.1%)
Load Regulation	$V_{in} = 15 \text{ V}, I_{o} = 0 \text{ A to } 1.0 \text{ A}$	25 mV (0.5%)
Output Ripple	$V_{in} = 10 \text{ V}, I_0 = 1.0 \text{ A}$	50 mVpp P.A.R.D.
Output Ripple	$V_{in} = 20 \text{ V}, I_0 = 1.0 \text{ A}$	100 mVpp P.A.R.D.
Efficiency	V <sub>in</sub> = 15 V, I <sub>o</sub> = 1.0 A	82%

#### **APPLICATIONS INFORMATION**

The TL431 is a programmable precision reference which is used in a variety of ways. It serves as a reference voltage in circuits where a non-standard reference voltage is needed. Other uses include feedback control for driving an optocoupler in power supplies, voltage monitor, constant current source, constant current sink and series pass regulator. In each of these applications, it is critical to maintain stability of the device at various operating currents and load capacitances. In some cases the circuit designer can estimate the stabilization capacitance from the stability boundary conditions curve provided in Figure 15. However, these typical curves only provide stability information at specific cathode voltages and at a specific load condition. Additional information is needed to determine the capacitance needed to optimize phase margin or allow for process variation.

A simplified model of the TL431 is shown in Figure 31. When tested for stability boundaries, the load resistance is 150  $\Omega$ . The model reference input consists of an input transistor and a dc emitter resistance connected to the device anode. A dependent current source, Gm, develops a current whose amplitude is determined by the difference between the 1.78 V internal reference voltage source and the input transistor emitter voltage. A portion of Gm flows through compensation capacitance,  $C_{P2}$ . The voltage across  $C_{P2}$  drives the output dependent current source, Go, which is connected across the device cathode and anode.

Model component values are:

 $V_{ref} = 1.78 \text{ V}$ 

 $Gm = 0.3 + 2.7 \exp(-I_C/26 \text{ mA})$ 

where I<sub>C</sub> is the device cathode current and Gm is in mhos

Go = 
$$1.25 (V_{cp}2) \mu mhos$$
.

Resistor and capacitor typical values are shown on the model. Process tolerances are  $\pm 20\%$  for resistors,  $\pm 10\%$  for capacitors, and  $\pm 40\%$  for transconductances.

An examination of the device model reveals the location of circuit poles and zeroes:

P1 = 
$$\frac{1}{2\pi R_{GM} C_{P1}}$$
 =  $\frac{1}{2\pi * 1.0 M * 20 pF}$  = 7.96 kHz

$$P2 = \frac{1}{2\pi R_{P2}C_{P2}} = \frac{1}{2\pi*10 M*0.265 pF} = 60 \text{ kHz}$$

$$Z1 = \frac{1}{2\pi R_{71}C_{P1}} = \frac{1}{2\pi * 15.9 k * 20 pF} = 500 kHz$$

In addition, there is an external circuit pole defined by the load:

$$P_L = \frac{1}{2\pi R_I C_I}$$

Also, the transfer dc voltage gain of the TL431 is:

$$G = G_M R_{GM} GoR_L$$

Example 1:

 $\rm I_{\mbox{\scriptsize C}} = 10\,m\mbox{\scriptsize mA}, R_{\mbox{\scriptsize L}} = \,230\,\Omega, C_{\mbox{\scriptsize L}} = \,0.$  Define the transfer gain .

The DC gain is:

$$G = G_M R_{GM} GoR_L =$$
(2.138)(1.0 M)(1.25  $\mu$ )(230) = 615 = 56 dB

Loop gain = G 
$$\frac{8.25 \text{ k}}{8.25 \text{ k} + 15 \text{ k}}$$
 = 218 = 47 dB

The resulting transfer function Bode plot is shown in Figure 32. The asymptotic plot may be expressed as the following equation:

$$Av = 615 \frac{\left(1 + \frac{jf}{500 \text{ kHz}}\right)}{\left(1 + \frac{jf}{8.0 \text{ kHz}}\right)\left(1 + \frac{jf}{60 \text{ kHz}}\right)}$$

The Bode plot shows a unity gain crossover frequency of approximately 600 kHz. The phase margin, calculated from the equation, would be 55.9 degrees. This model matches the Open–Loop Bode Plot of Figure 12. The total loop would have a unity gain frequency of about 300 kHz with a phase margin of about 44 degrees.

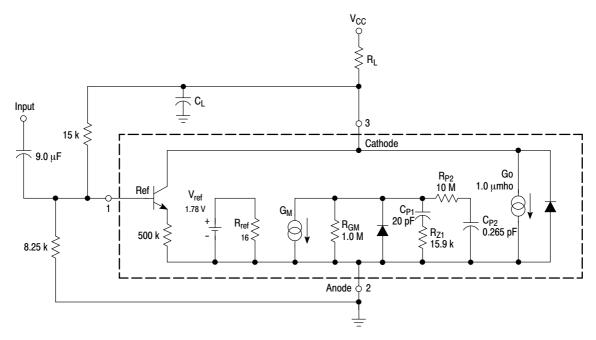


Figure 31. Simplified TL431 Device Model

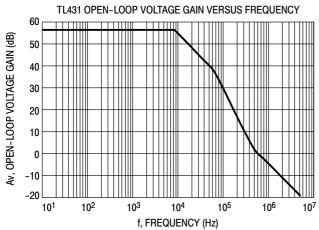


Figure 32. Example 1 Circuit Open Loop Gain Plot Example 2.

 $I_C$  = 7.5 mA,  $R_L$  = 2.2 k $\Omega$ ,  $C_L$  = 0.01  $\mu$ F. Cathode tied to reference input pin. An examination of the data sheet stability boundary curve (Figure 15) shows that this value of load capacitance and cathode current is on the boundary. Define the transfer gain.

The DC gain is:

$$G = G_M R_{GM} GoR_L =$$

 $(2.323)(1.0 \text{ M})(1.25 \mu)(2200) = 6389 = 76 \text{ dB}$ 

The resulting open loop Bode plot is shown in Figure 33. The asymptotic plot may be expressed as the following equation:

$$Av = 615 \frac{\left(1 + \frac{jf}{500 \text{ kHz}}\right)}{\left(1 + \frac{jf}{8.0 \text{ kHz}}\right)\!\left(1 + \frac{jf}{60 \text{ kHz}}\right)\!\left(1 + \frac{jf}{7.2 \text{ kHz}}\right)}$$

Note that the transfer function now has an extra pole formed by the load capacitance and load resistance.

Note that the crossover frequency in this case is about 250 kHz, having a phase margin of about -46 degrees. Therefore, instability of this circuit is likely.

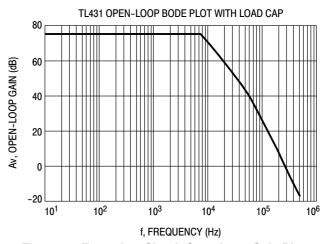


Figure 33. Example 2 Circuit Open Loop Gain Plot

With three poles, this system is unstable. The only hope for stabilizing this circuit is to add a zero. However, that can only be done by adding a series resistance to the output capacitance, which will reduce its effectiveness as a noise filter. Therefore, practically, in reference voltage applications, the best solution appears to be to use a smaller value of capacitance in low noise applications or a very large value to provide noise filtering and a dominant pole rolloff of the system.

#### **ORDERING INFORMATION**

Device	Marking Code	Operating Temperature Range	Package Code	Shipping Information <sup>†</sup>	Tolerance
TL431ACD			SOIC-8		
TL431ACDG	AC		SOIC-8 (Pb-Free)		1.0%
TL431BCDG	ВС		SOIC-8 (Pb-Free)	98 Units / Rail	0.4%
TL431CD			SOIC-8		2.2%
TL431CDG	С		SOIC-8 (Pb-Free)		2.2%
TL431ACDR2			SOIC-8		
TL431ACDR2G	AC		SOIC-8 (Pb-Free)		1.0%
TL431BCDR2G	ВС		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	0.4%
TL431CDR2G	С		SOIC-8 (Pb-Free)		2.2%
TL431ACDMR2G	TAC		Micro8 (Pb-Free)		1.0%
TL431BCDMR2G	TBC		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
TL431CDMR2G	T-C		Micro8 (Pb-Free)		2.2%
TL431ACPG	ACP		PDIP-8 (Pb-Free)		1.0%
TL431BCPG	ВСР		PDIP-8 (Pb-Free)	50 Units / Rail	0.4%
TL431CPG	СР	0°C to 70°C	PDIP-8 (Pb-Free)		2.2%
TL431ACLPG	ACLP		TO-92 (Pb-Free)		1.0%
TL431BCLPG	BCLP		TO-92 (Pb-Free)	2000 Units / Bag	0.4%
TL431CLP			TO-92		
TL431CLPG	CLP		TO-92 (Pb-Free)		2.2%
TL431ACLPRA			TO-92		
TL431ACLPRAG	ACLP		TO-92 (Pb-Free)	2000 Units / Tape & Reel	1.0%
TL431BCLPRAG	BCLP		TO-92 (Pb-Free)		0.4%
TL431CLPRAG	CLP		TO-92 (Pb-Free)	2000 Haita / Tana <sup>9</sup> Baal	2.2%
TL431ACLPREG	ACLP		TO-92 (Pb-Free)	2000 Units / Tape & Reel	1.0%
TL431BCLPREG	BCLP		TO-92 (Pb-Free)		0.4%
TL431ACLPRPG	ACLP		TO-92 (Pb-Free)	2000 / Tape & Ammo Box	1.0%
TL431BCLPRMG	BCLP		TO-92 (Pb-Free)		0.4%
TL431CLPRP			TO-92	2000 Units / Fan-Fold	
TL431CLPRPG	CLP		TO-92 (Pb-Free)		2.2%

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ORDERING INFORMATION**

Device	Marking Code	Operating Temperature Range	Package Code	Shipping Information <sup>†</sup>	Tolerance
TL431AIDG	Al		SOIC-8 (Pb-Free)		1.0%
TL431BID			SOIC-8		
TL431BIDG	BI		SOIC-8 (Pb-Free)	98 Units / Rail	0.4%
TL431IDG	I		SOIC-8 (Pb-Free)		2.2%
TL431AIDR2G	Al		SOIC-8 (Pb-Free)		1.0%
TL431BIDR2			SOIC-8		
TL431BIDR2G	BI	-40°C to 85°C	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	0.4%
TL431IDR2			SOIC-8		
TL431IDR2G	'		SOIC-8 (Pb-Free)		2.2%
TL431AIDMR2G	TAI		Micro8 (Pb-Free)		1.0%
TL431BIDMR2G	ТВІ		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
TL431IDMR2G	T-I		Micro8 (Pb-Free)		2.2%
TL431AIPG	AIP		PDIP-8 (Pb-Free)		1.0%
TL431BIPG	BIP		PDIP-8 (Pb-Free)	50 Units / Rail	0.4%
TL431IPG	IP		PDIP-8 (Pb-Free)		2.2%
TL431AILPG	AILP		TO-92 (Pb-Free)		1.0%
TL431BILPG	BILP		TO-92 (Pb-Free)	2000 Units / Bag	0.4%
TL431ILPG	ILP		TO-92 (Pb-Free)		2.2%
TL431AILPRAG	AILP	–40°C to 85°C	TO-92 (Pb-Free)		1.0%
TL431BILPRAG	BILP		TO-92 (Pb-Free)	2000 Units / Tape & Reel	0.4%
TL431ILPRAG	ILP		TO-92 (Pb-Free)		2.2%
TL431AILPRMG			TO-92 (Pb-Free)		1.0%
TL431AILPRPG	AILP		TO-92 (Pb-Free)	2000 / Tape & Ammo Box	1.0%
TL431ILPRPG	ILP		TO-92 (Pb-Free)		2.2%

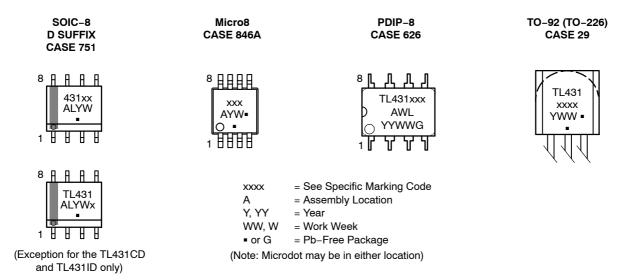
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ORDERING INFORMATION**

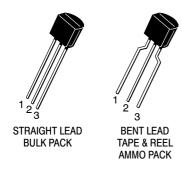
Device	Marking Code	Operating Temperature Range	Package Code	Shipping Information <sup>†</sup>	Tolerance
TL431BVDG	BV		SOIC-8 (Pb-Free)	98 Units / Rail	0.4%
TL431BVDR2G	DV		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	0.4%
TL431BVDMR2G	TBV		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
TL431BVLPG	D) (I D		TO-92 (Pb-Free)	2000 Units / Bag	0.4%
TL431BVLPRAG	BVLP	-40°C to 125°C	TO-92 (Pb-Free)	2000 Units / Tape & Reel	0.4%
TL431BVPG	BVP		PDIP-8 (Pb-Free)	50 Units / Rail	0.4%
NCV431AIDMR2G	RAN		Micro8 (Pb-Free)	4000 Units / Tape & Reel	1%
NCV431AIDR2G	AV		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	1%
NCV431BVDMR2G	NVB		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

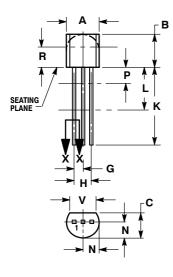
#### **MARKING DIAGRAMS**



#### PACKAGE DIMENSIONS



TO-92 (TO-226) CASE 29-11 **ISSUE AM** 



STRAIGHT LEAD **BULK PACK** 



- NOTES:

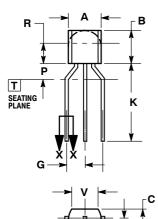
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD TAPE & REEL** AMMO PACK



- NOTES:

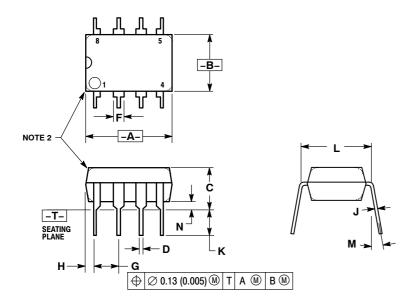
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P

- AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS					
DIM	MIN	MAX				
Α	4.45	5.20				
В	4.32	5.33				
С	3.18	4.19				
D	0.40	0.54				
G	2.40	2.80				
J	0.39	0.50				
K	12.70					
N	2.04	2.66				
P	1.50	4.00				
R	2.93					
٧	3.43					

#### **PACKAGE DIMENSIONS**

PDIP-8 **P SUFFIX** PLASTIC PACKAGE CASE 626-05 ISSUE L

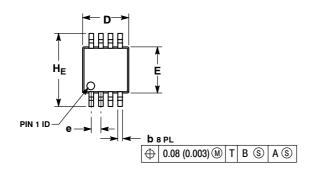


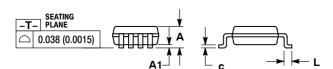
- NOTES:
  1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
  3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.40	10.16	0.370	0.400	
В	6.10	6.60	0.240	0.260	
U	3.94	4.45	0.155	0.175	
D	0.38	0.51	0.015	0.020	
F	1.02	1.78	0.040	0.070	
G	2.54	BSC	0.100 BSC		
H	0.76	1.27	0.030	0.050	
7	0.20	0.30	0.008	0.012	
K	2.92	3.43	0.115	0.135	
L	7.62		0.300	BSC	
M		10°		10°	
N	0.76	1.01	0.030	0.040	

#### PACKAGE DIMENSIONS

#### Micro8 **DM SUFFIX** PLASTIC PACKAGE CASE 846A-02 **ISSUE G**





- AUTES:

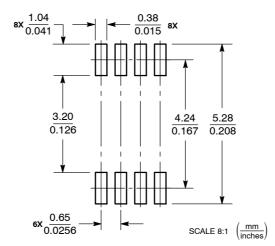
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. 846A-01 OBSOLETE, NEW STANDARD 846A-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α			1.10			0.043
A1	0.05	0.08	0.15	0.002	0.003	0.006
b	0.25	0.33	0.40	0.010	0.013	0.016
С	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
E	2.90	3.00	3.10	0.114	0.118	0.122
е	0.65 BSC			0.026 BSC		
L	0.40	0.55	0.70	0.016	0.021	0.028
HE	4.75	4.90	5.05	0.187	0.193	0.199

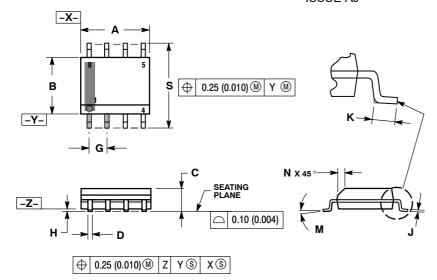
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **PACKAGE DIMENSIONS**

#### SOIC-8 **D SUFFIX** PLASTIC PACKAGE CASE 751-07 **ISSUE AJ**



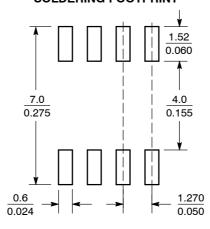
#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A AND B DO NOT INCLUDE
- MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
- MAXIMUM MATERIAL CONDITION. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
O	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
Κ	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***



 $\left(\frac{\text{mm}}{\text{inches}}\right)$ 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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